

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket Number (Optional) NSC1-H2610	Application Number New <u>10/669045</u>
	Applicant(s) <u>Alexei Sadovnikov</u>	
	Filing Date Herewith	Group Art Unit <u>Unknown 2815</u>

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>My</i>	*AA	5,698,890	12/16/97	Sato	257	592	09/12/95
	*AB	2003/0001235 A1	01/02/03	Hashimoto	257	592	08/29/02
	*AC	5,494,836	02/27/96	Imai	437	31	06/02/95
	*AD	5,250,448	10/05/93	Hamasaki et al.	437	31	01/31/91
	*AE	5,016,075	05/14/91	Minato	357	35	10/16/89
	*AF	5,412,228	05/02/95	Baliga	257	133	02/10/94
	*AG	5,440,152	08/08/95	Yamazaki	257	197	11/28/94
	*AH	5,041,892	08/20/91	Yano et al.	357	34	05/14/90
	*AI	5,340,753	08/23/94	Bassous et al.	437	31	04/14/93
	*AJ	5,315,151	05/24/94	Hsieh et al.	257	592	02/22/93
	*AK	5,930,635	07/27/99	Bashir et al.	438	313	05/02/97
	*AL	6,346,453 B1	02/12/02	Kovacic et al.	438	312	01/27/00
	*AM	5,789,800	08/04/98	Kohno	257	588	01/17/97
<i>My</i>	*AN	6,337,494 B1	01/08/02	Ryum et al.	257	197	08/21/98
	*AO	5,668,396	09/16/97	Sato	257	517	09/25/95

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<i>My</i>	*AP	EP 1 139 408 A2	10/04/01	Europe	H01L	21/331	X	

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

<i>My</i>	*AQ	A. Schuppen et al. "Enhanced SiGe Heterojunction Bipolar Transistors with 160 GHz- f_{max} ", IEDM 95 743-746, 1995 IEEE.
	*AR	Denny D. Tang, "A Reduced-Field Design Concept for High-Performance Bipolar Transistors", IEEE Electron Device Letters, Vol. 10, No. 2, February 1989, pp 67-69.

Examiner <u><i>Don G. Featz</i></u>	Date Considered <u><i>7/19/04</i></u>
Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	